





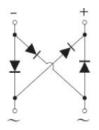
RMB2S-RMB6S Miniature Glass Passivated Fast Recovery Surface Mount Bridge Rectifiers



Features

- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- High temperature soldering guaranteed:260° C/ 10 seconds at 5 lbs., (2.3kg) tension
- · Small size, simple installation
- High surge current capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: Molded plastic body
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026
- Polarity: Polarity symbols marked on case
- Mounting Position: Any
- Weight: 0.0044 ounce, 0.126 grams

Maximum Ratings @T_A=25°C unless otherwise specified

Type number	Symbol	RMB2S	RMB4S	RMB6S	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM}	200	400	600	V
RMS Reverse Voltage	V _{RMS}	140	280	420	V
Maximum average forward current 60Hz sine save resistance load On glass-epoxy P.C.B. On aluminum substrate	I _{F(AV)}	0.5 0.8		А	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30		А	

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Electrical Characteristics:

Type number	Symbol	RMB2S	RMB4S	RMB6S	Units
Maximum instantaneous forward voltage drop (Note 1)@ I _F = 0.4A	V _F	1.0			V
Maximum DC reverse current $T_A = 25^{\circ}C$ at rated DC blocking voltage $T_A = 125^{\circ}C$	I _R	5 100		μA	
Maximum reverse recovery time(Note 2)	trr	150		nS	
Typical junction capacitance (per leg)	Cj		13		pF

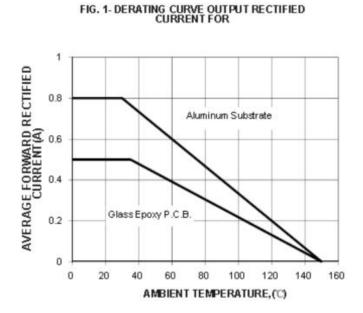
^{*} Pulse width < 300 μ s, duty cycle < 2%

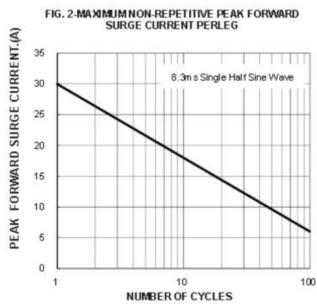
Thermal-Mechanical Specifications:

Type number	Symbol	RMB2S	RMB4S	RMB6S	Units
Typical thermal resistance	$R_{\theta JA}$	85		°C/W	
Operating junction and storage temperature range	T _J ,T _{STG}	-55 to +150		°C	

- Note: 1. Mounted on glass epoxy PC board with 1.3mm² solder pad..
 - 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
 - 3. Thermal Resistance From Junction to Ambient

Ratings and Characteristics Curves



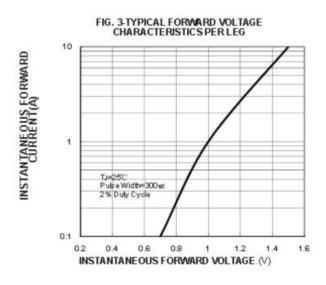


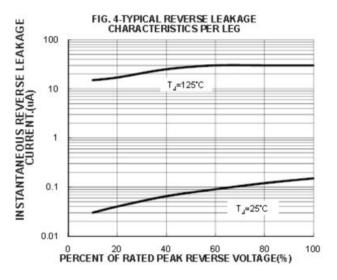
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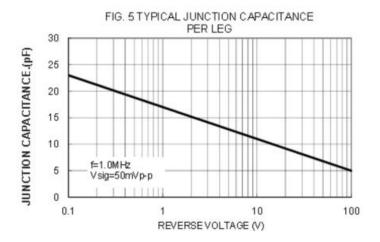










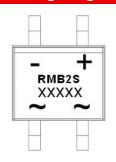


Ordering Information

Device	Package	Shipping
RMB2S THRU RMB6S	MB-S (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

 RMB2S
 = Type Number

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

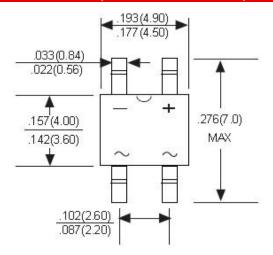
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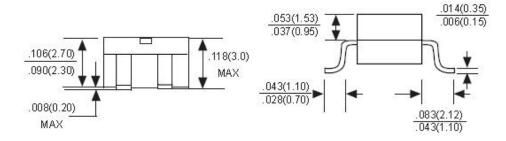




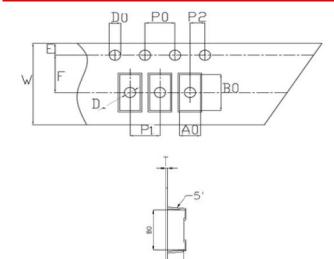


Mechanical Dimensions MB-S(Inches/Millimeters)





Carrier Tape Specification MB-S



SYMBOL	Millimeters			
STWBOL	Min.	Max.		
A0	4.92	5.12		
B0	7.12	7.32		
D0	1.50	1.60		
D1	1.40	1.60		
P0	3.90	4.10		
P1	7.90	8.10		
P2	1.95	2.05		
E	1.65	1.85		
K0	2.78	2.98		
F	5.45	5.55		
W	11.90	12.10		
Т	0.24	0.30		
10P0	39.80	40.20		
抗拉拉力	≥3KG			

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